

MST500.18-B0

Thyristor module

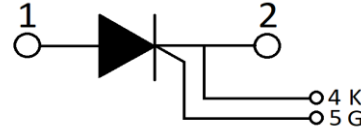


Features:

- Pressure contact technology with increased power cycling capability
- Glass passivated chip
- Simple mounting
- UL recognized, file no. E312789

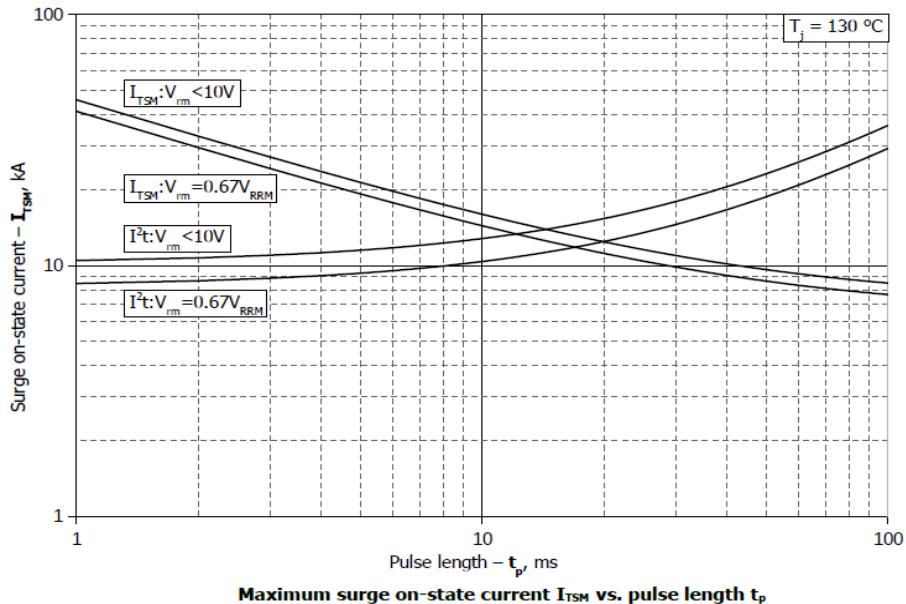
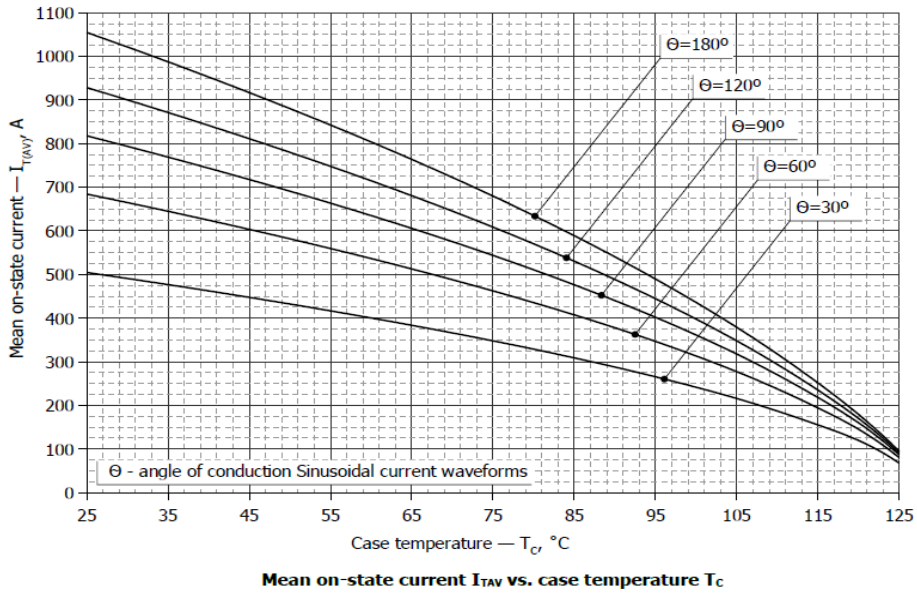
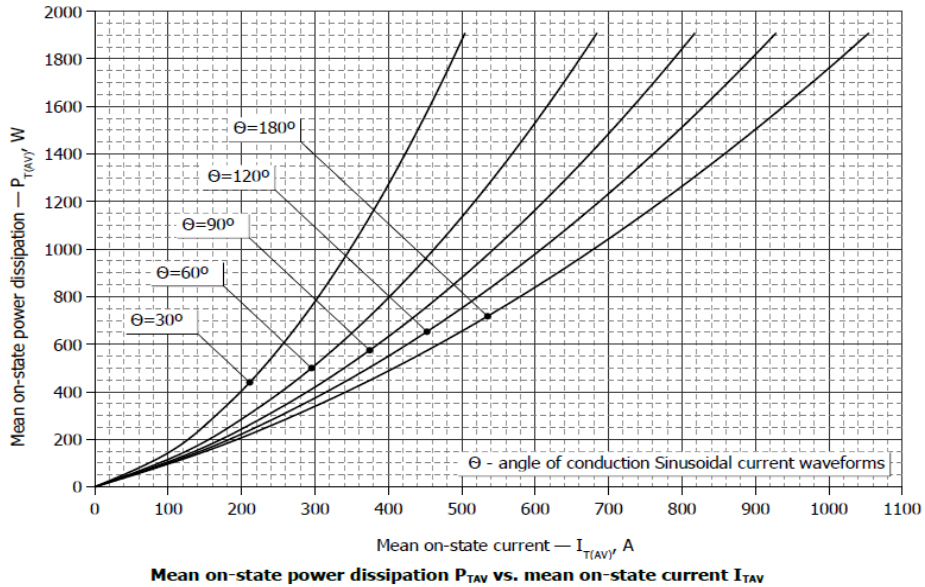
Typical applications:

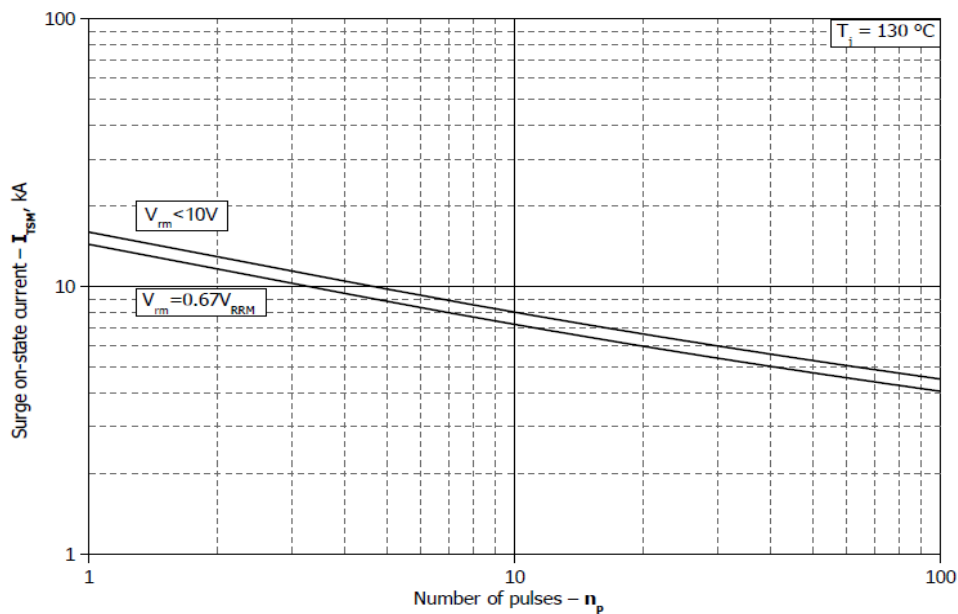
- Power converters
- Lighting control
- DC motor control and drives
- Heat and temperature control



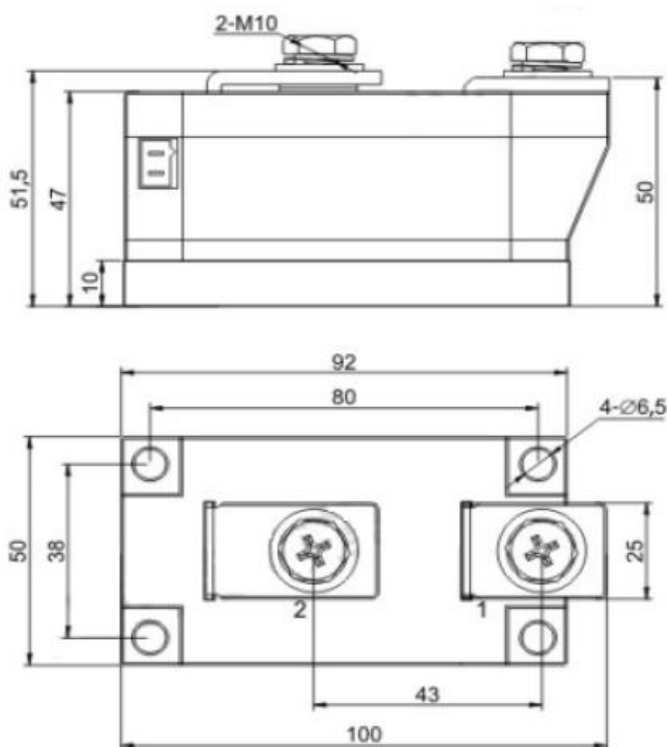
Symbol	Characteristics	Test Conditions	Value			Unit
			Min	Typ	Max	
$V_{RSM/DSM}$	Non-repetitive reverse/forward blocking voltage	$T_j = 25^\circ\text{C}$			1900	V
$V_{RRM/DRM}$	Repetitive reverse/forward blocking voltage	$T_j = 25^\circ\text{C}$			1800	V
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz			500	A
$I_{T(RMS)}$	RMS on-state current	$T_c = 94^\circ\text{C}$			785	A
I_{RRM} I_{DRM}	Repetitive peak current	at V_{DRM}/V_{RRM} $T_j = 130^\circ\text{C}$			70	mA
I_{TSM}	Surge non repetitive current	10ms half sine wave $V_R = 60\% V_{RRM}$ $T_j = 130^\circ\text{C}$			22	kA
$I^2 t$	$I^2 t$ for fusing coordination				1200	kA^2s
V_{TO}	Threshold voltage	$T_j = 130^\circ\text{C}$			0.858	V
r_T	On-state slope resistance	$T_j = 130^\circ\text{C}$			0.366	$\text{m}\Omega$
V_{TM}	Peak on-state voltage	$T = 25^\circ\text{C}$; $I_T = 1570\text{A}$			1.50	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM}$, $T_j = 130^\circ\text{C}$, linear voltage rise			1000	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of off-state current	$T_j = 130^\circ\text{C}$, Gate source 2A, $I_{TM} = 2000\text{A}$, $T_r < 0,5\mu\text{s}$ Non- Repetitive			1250	$\text{A}/\mu\text{s}$
I_{GT}	Gate trigger current				250	mA
V_{GT}	Gate trigger voltage	$V_A = 12\text{V}$, $I_A = 1\text{A}$, $T_j = 25^\circ\text{C}$			2.5	V
I_H	Holding current				300	mA
V_{GD}	Non-trigger gate voltage	$V_{DM} = 67\% V_{DRM}$, $T_j = 130^\circ\text{C}$			0.30	V
$R_{th(j-c)}$	Thermal resistance junction to case	Single side cooled per chip			0.055	$^\circ\text{C}/\text{W}$
$R_{th(c-s)}$	Thermal resistance case to sink	Single side cooled per chip			0.010	$^\circ\text{C}/\text{W}$
V_{ISO}	Isolation voltage	50Hz, RMS, $t = 1\text{min}$, $I_{ISO} : 1\text{mA (MAX)}$	3000			V
F_M	Mounting torque - copper plate (M6)		4.5		6.0	N·m
	Mounting torque - terminal (M12)		10		12	N·m
T_{stg}	Storage Temperature		-40		130	$^\circ\text{C}$
T_j	Operating Temperature		-40		130	$^\circ\text{C}$
W_t	Weight			900		g
Outline		B0				

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Maximum surge on-state current I_{TSM} vs. number of pulses n_p



(dimensions in mm)

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